RELIABILITY REPORT

FOR

MAX339ESE+

PLASTIC ENCAPSULATED DEVICES

October 3, 2012

MAXIM INTEGRATED

160 RIO ROBLES

SAN JOSE, CA 95134

Approved by
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Conclusion

The MAX339ESE+ successfully meets the quality and reliability standards required of all Maxim Integrated products. In addition, Maxim Integrated's continuous reliability monitoring program ensures that all outgoing product will continue to meet Maxim Integrated's quality and reliability standards.

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I. Device Description

A. General

The MAX338/MAX339 are monolithic, CMOS analog multiplexers (muxes). The 8-channel MAX338 is designed to connect one of eight inputs to a common output by control of a 3-bit binary address. The dual, 4-channel MAX339 is designed to connect one of four inputs to a common output by control of a 2-bit binary address. Both devices can be used as either a mux or a demux. On-resistance is 400 max, and the devices conduct current equally well in both directions. These muxes feature extremely low off leakages (less than 20pA at +25°C), and extremely low on-channel leakages (less than 50pA at +25°C). The new design offers guaranteed low charge injection (1.5pC typ) and electrostatic discharge (ESD) protection greater than 2000V, per method 3015.7. These improved muxes are pin-compatible upgrades for the industry-standard DG508A and DG509A. For similar Maxim devices with lower leakage and charge injection but higher on-resistance, see the MAX328 and MAX329. The MAX338/MAX339 operate from a single +4.5V to +30V supply or from dual supplies of ±4.5V to ±20V. All control inputs (whether address or enable) are TTL compatible (+0.8V to +2.4V) over the full specified temperature range and over the ±4.5V to ±18V supply range. These parts are fabricated with Maxim's 44V silicon-gate process.

II. Manufacturing Information

A. Description/Function:	8-Channel/Dual 4-Channel, Low-Leakage, CMOS Analog Multiplexers
B. Process:	S5
C. Number of Device Transistors:	
D. Fabrication Location:	Oregon, California
E. Assembly Location:	Malaysia, Thailand, Philippines
F. Date of Initial Production:	Pre 1997

III. Packaging Information

A. Package Type:	16-pin SOIC (N)
B. Lead Frame:	Copper
C. Lead Finish:	100% matte Tin
D. Die Attach:	Conductive
E. Bondwire:	Au (1.3 mil dia.)
F. Mold Material:	Epoxy with silica filler
G. Assembly Diagram:	#05-0301-0654
H. Flammability Rating:	Class UL94-V0
I. Classification of Moisture Sensitivity per JEDEC standard J-STD-020-C	Level 1
J. Single Layer Theta Ja:	115°C/W
K. Single Layer Theta Jc:	32°C/W
L. Multi Layer Theta Ja:	82.2°C/W
M. Multi Layer Theta Jc:	32°C/W

IV. Die Information

A. Dimensions:	78 X 114 mils
B. Passivation:	Si_3N_4/SiO_2 (Silicon nitride/ Silicon dioxide)
C. Interconnect:	Al/0.5%Cu with Ti/TiN Barrier
D. Backside Metallization:	None
E. Minimum Metal Width:	5.0 microns (as drawn)
F. Minimum Metal Spacing:	5.0 microns (as drawn)
G. Bondpad Dimensions:	
H. Isolation Dielectric:	SiO_2
I. Die Separation Method:	Wafer Saw

V. Quality Assurance Information

A. Quality Assurance Contacts:	Richard Aburano (Manager, Reliability Engineering) Don Lipps (Manager, Reliability Engineering) Bryan Preeshl (Vice President of QA)
B. Outgoing Inspection Level:	0.1% for all electrical parameters guaranteed by the Datasheet. 0.1% For all Visual Defects.
C. Observed Outgoing Defect Rate:	< 50 ppm
D. Sampling Plan:	Mil-Std-105D

VI. Reliability Evaluation

A. Accelerated Life Test

The results of the 135°C biased (static) life test are shown in Table 1. Using these results, the Failure Rate (λ) is calculated as follows:

$$\lambda = \frac{1}{MTTF} = \frac{1.83}{1000 \times 4340 \times 160 \times 2}$$ (Chi square value for MTTF upper limit)

(where 4340 = Temperature Acceleration factor assuming an activation energy of 0.8eV)

$\lambda = 1.3 \times 10^{-9}$

λ = 1.3 F.I.T. (60% confidence level @ 25°C)

The following failure rate represents data collected from Maxim Integrated's reliability monitor program. Maxim Integrated performs quarterly life test monitors on its processes. This data is published in the Reliability Report found at http://www.maximintegrated.com/qa/reliability/monitor. Cumulative monitor data for the S5 Process results in a FIT Rate of 0.09 @ 25C and 1.55 @ 55C (0.8 eV, 60% UCL)

B. E.S.D. and Latch-Up Testing (ESD lot XDSBBQ001A D/C 9447, Latch-Up lot NDSBC1001C D/C 9912)

The AG65-1 die type has been found to have all pins able to withstand a HBM transient pulse of +/-1000V per Mil-Std 883 Method 3015.7. Latch-Up testing has shown that this device withstands a current of +/-250mA.

Table 1
Reliability Evaluation Test Results

MAX339ESE+

TEST ITEM	TEST CONDITION	FAILURE IDENTIFICATION	SAMPLE SIZE	NUMBER OF FAILURES	COMMENTS
Static Life Test (Note 1)					
	Ta = 135°C	DC Parameters	80	0	NDSBCA063C, D/C 0513
	Biased	& functionality	80	0	NDSAC2038C, D/C 0329
	Time = 1000 hrs.				

Note 1: Life Test Data may represent plastic DIP qualification lots.